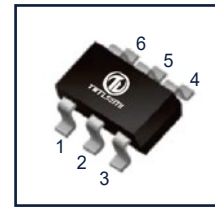
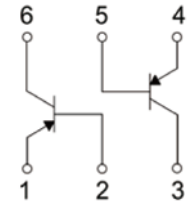


Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching



SOT-363



Equivalent Circuit

Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-40	V
V_{CE0}	Collector-Emitter Voltage	-40	V
V_{EB0}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.6	A
P_C	Collector Power Dissipation	0.2	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	$^{\circ}\text{C}/\text{W}$
$T_{j,Tstg}$	Operation Junction And Storage Temperature Range	-55 ~ +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-100\mu\text{A}, I_E=0$	-40			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1\text{mA}, I_B=0$	-40			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-100\mu\text{A}, I_C=0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB}=-35\text{V}, I_E=0$			-0.1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
$h_{FE(1)}$	DC current gain	$V_{CE}=-1\text{V}, I_C=-0.1\text{mA}$	30			
$h_{FE(2)}$		$V_{CE}=-1\text{V}, I_C=-1\text{mA}$	60			
$h_{FE(3)}$		$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100			
$h_{FE(4)}$		$V_{CE}=-2\text{V}, I_C=-150\text{mA}$	100		300	
$h_{FE(5)}$		$V_{CE}=-2\text{V}, I_C=-500\text{mA}$	20			
$V_{CE(sat)(1)}$	Collector-emitter saturation voltage	$I_C=-150\text{mA}, I_B=-15\text{mA}$			-0.4	V
$V_{CE(sat)(2)}$		$I_C=-500\text{mA}, I_B=-50\text{mA}$			-0.75	V
$V_{BE(1)}$	Base-emitter voltage	$I_C=-150\text{mA}, I_B=-15\text{mA}$	-0.75		-0.95	V
$V_{BE(2)}$		$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1.3	V
f_T	Transition frequency	$V_{CE}=-10\text{V}, I_C=-20\text{mA}, f=100\text{MHz}$	200			MHz
C_{ob}	Output Capacitance	$V_{CB}=-10\text{V}, I_E=0\text{A}, f=1\text{MHz}$			8.5	pF
t_d	Delay time	$V_{CC}=-30\text{V}, V_{BE}=-2\text{V}, I_C=-150\text{mA}, I_{B1}=-15\text{mA}$			15	nS
t_r	Rise time				20	nS
t_s	Storage time	$V_{CC}=-30\text{V}, I_C=-150\text{mA}, I_{B1}=I_{B2}=-15\text{mA}$			225	nS
t_f	Fall time				30	nS

Ordering information

Product ID	Pack	Naming rule	Marking	$h_{FE(1)}$	Qty(PCS)
MMDT4403	SOT-363	MMDT4403 产品名称 product name	K2T	100-300	3000



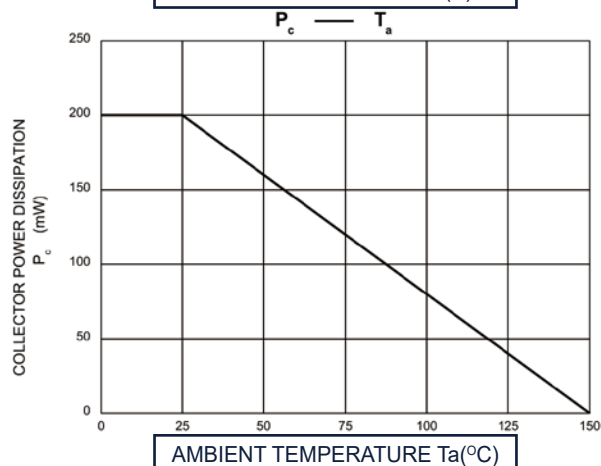
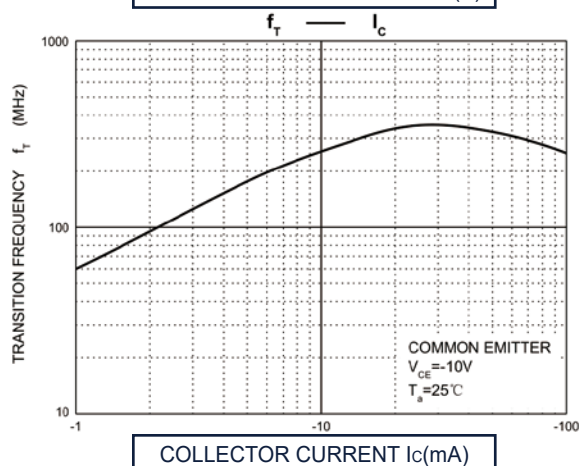
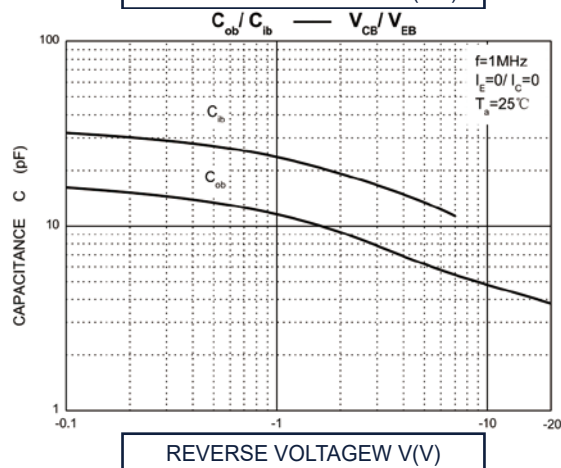
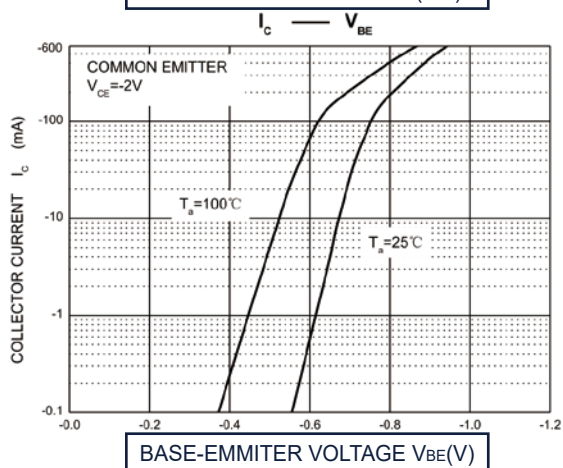
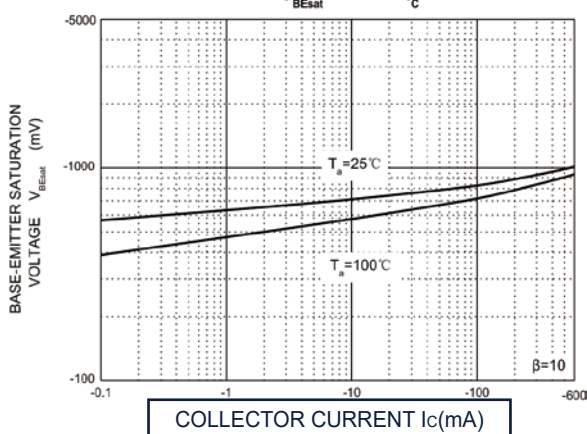
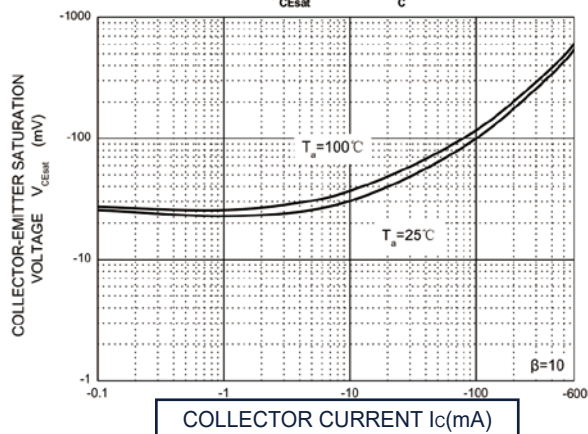
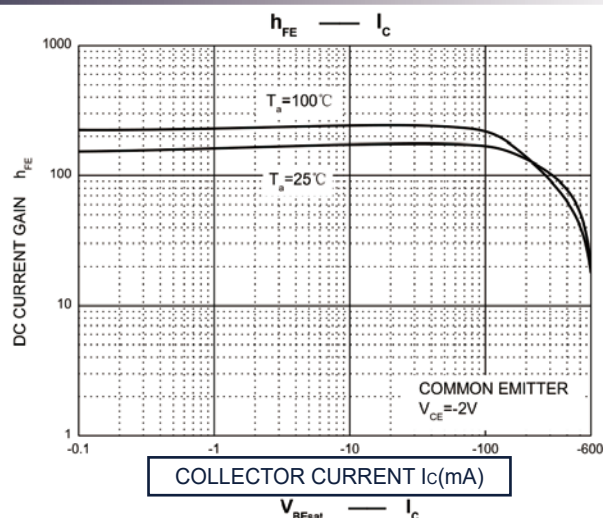
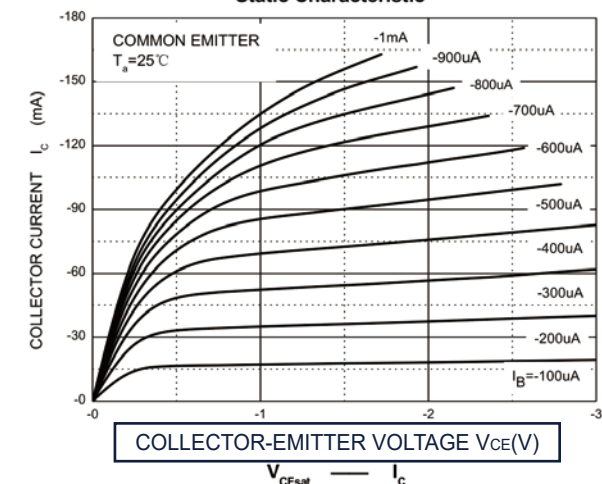
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SOT-363 DUAL TRANSISTOR (PNP+PNP)

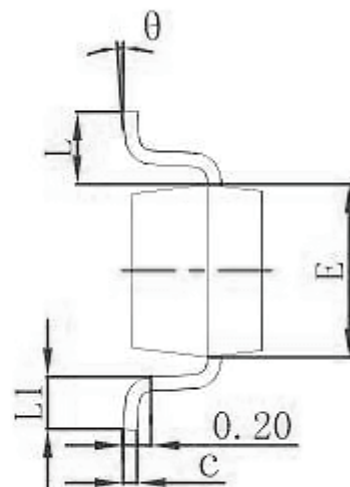
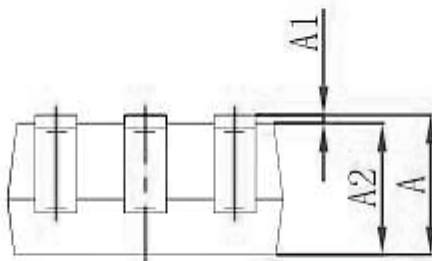
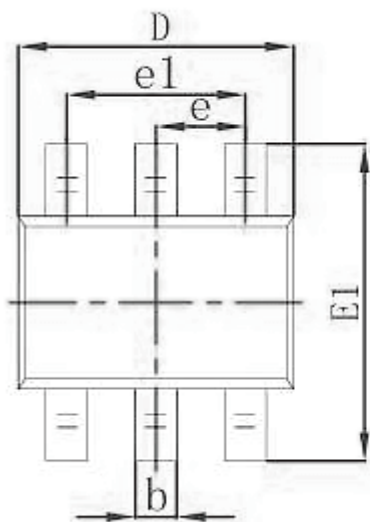
Typical Characteristics

Static Characteristic





SOT-363 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°